



#### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D MAX</sub> T <sub>C</sub> = +25°C	
60V	6.2mΩ @ V <sub>GS</sub> = 10V	100A	

# Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

PowerDI5060-8

- Synchronus Rectifier
- DC-DC Converters
- Power Management

#### **Features**

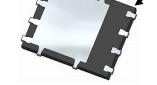
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

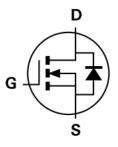
- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.097 grams (Approximate)



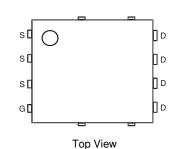
Top View



Bottom View







Pin Configuration

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6006SPS-13	PowerDI5060-8	2,500 / Tape & Reel

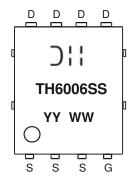
Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

Pin1

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



D:: = Manufacturer's Marking TH6006SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Dunin Comunet (Nata 5) V 40V	T <sub>A</sub> = +25°C	1	17.8	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>A</sub> = +100°C	ID	12.6	
Continuous Dusin Comment (Nets C) V 40V	T <sub>C</sub> = +25°C	1	100.0	Α
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	T <sub>C</sub> = +100°C	ID	75.9	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	400	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	100	Α	
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	400	Α	
Avalanche Current, L = 0.3mH	I <sub>AS</sub>	24.2	Α	
Avalanche Energy, L = 0.3mH	E <sub>AS</sub>	87.9	mJ	

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	2.94	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	51	°C/W	
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	$P_{D}$	107	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1.4	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

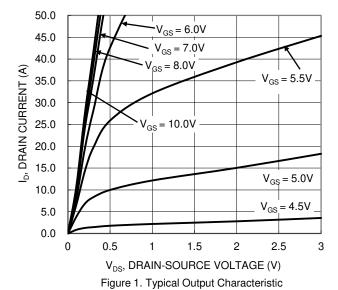
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	1	4	٧	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	4.8	6.2	mΩ	$V_{GS} = 10V, I_D = 10.5A$	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 21A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		1721			$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	1	740	1	pF		
Reverse Transfer Capacitance	Crss	_	49	_			
Gate Resistance	$R_g$	_	0.6	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qq	_	27.9	_			
Gate-Source Charge	Qgs	_	7.4	_	nC	$V_{DS} = 30V$ , $I_D = 21A$ , $V_{GS} = 10V$	
Gate-Drain Charge	$Q_{gd}$	_	7.3	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.5	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 10.5A, R_{q} = 4.7\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	8.2	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>		16.5		ns		
Turn-Off Fall Time	t <sub>F</sub>		9.8				
Reverse Recovery Time	t <sub>RR</sub>	_	37.0	_	ns		
Reverse Recovery Charge	QRR	_	42.9	_	nC	I <sub>F</sub> = 21A, di/dt = 300A/μs	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







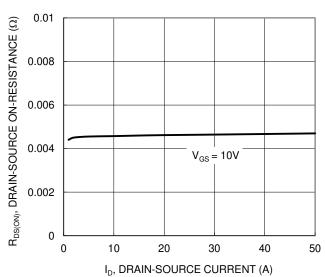


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

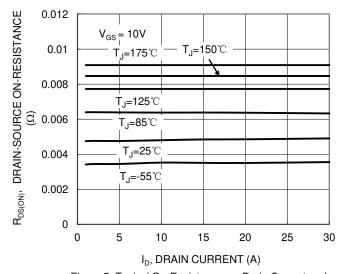
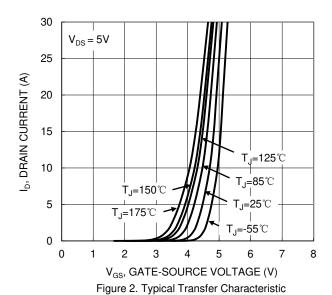


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



0.05  $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.04 0.03 0.02  $I_{D} = 10.5A$ 0.01 0

8

0

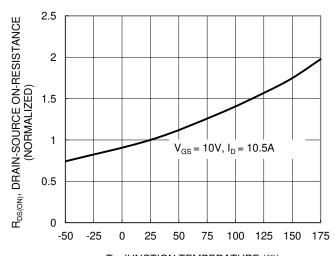
4

 $V_{GS}$ , GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

12

16

20



 $T_J$ , JUNCTION TEMPERATURE ( $^{\circ}$ C) Figure 6. On-Resistance Variation with Junction Temperature





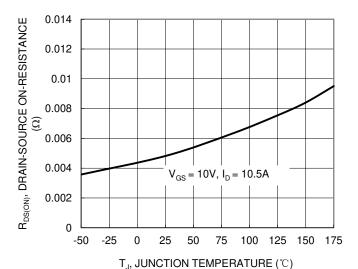


Figure 7. On-Resistance Variation with Junction Temperature

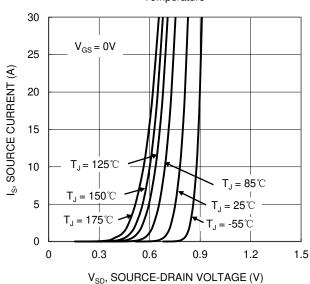


Figure 9. Diode Forward Voltage vs. Current

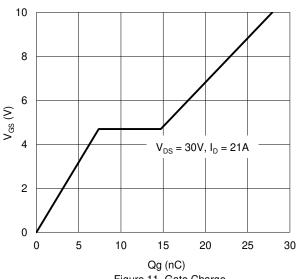


Figure 11. Gate Charge

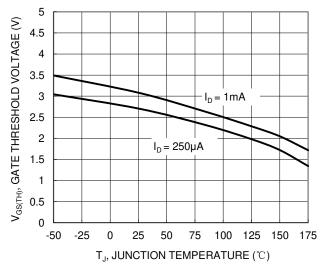
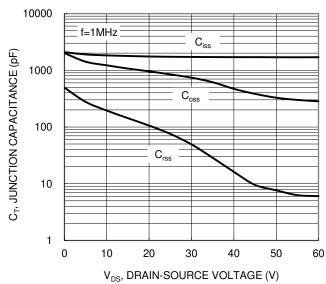


Figure 8. Gate Threshold Variation vs. Junction Temperature



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance

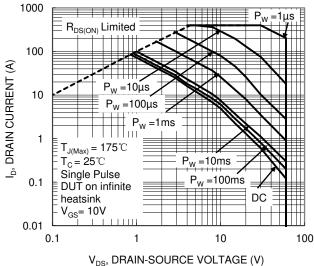


Figure 12. SOA, Safe Operation Area



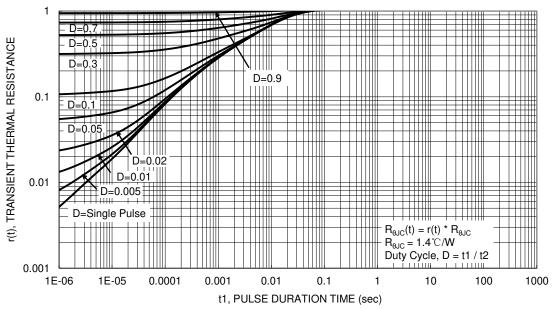


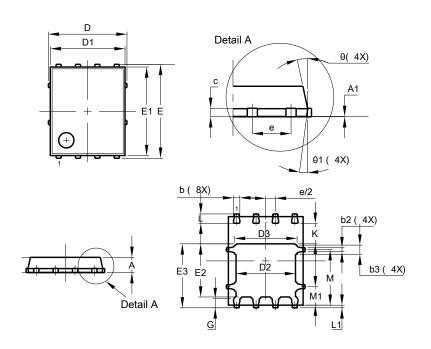
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

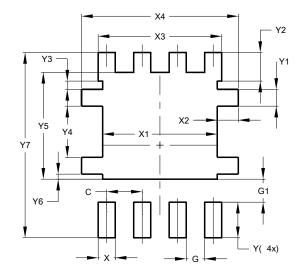


PowerDI5060-8					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0.00	0.05	1		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	ļ,	5.15 BSC	,		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(	6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			

**April 2019** 



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